TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA8119P

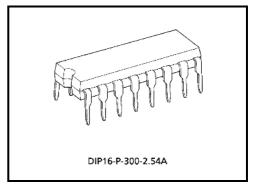
Stereo Headphone Amplifier (3V USE)

The TA8119P is developed for play-back stereo headphone player (3V use), which is built-in preamplifiers, power amplifiers (for headphone) and DC volume controls.

Features

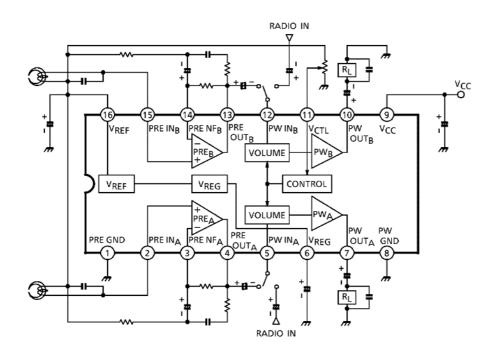
- Built-in DC volume controls
- Coupling condenser-less for input of preamplifier
- The loop gain of power amplifier is 30dB (typ.), in case that DC volume is at maximum
- Available of external input signal from DC volume stage
- Low quiescent current (VCC = 3V, Ta = 25°C) ICCQ = 9mA (typ.)
- Operating supply voltage range (Ta = 25°C)

$$V_{CC (opr)} = 1.8 \sim 6V$$



Weight: 1.00g (typ.)

Block Diagram



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Pin Function Terminal Voltage: Typical Terminal Voltage at no Signal with Test Circuit (V_{CC} = 3V, Ta = 25°C)

Pin No.	Pin Name	Contents	Equivalent	Terminal Voltage (V)	
1	PRE GND	_	_	0	
2	PRE IN _A	Input of preamplifier	from V _{REG}	1.3	
15	PRE IN _B	input of preampline	Ψ	1.5	
3	PRE NF _A		(15) (14)		
14	PRE NF _B	NF of preamplifier	1.3		
4	PRE OUT _A		from V _{REG}		
13	PRE OUT _B	Output of preamplifier	1.3		
5	PW IN _A		Vcc & O(n)		
12	PW IN _B	Input of power amplifier for headphone (through DC volume stage)	VCC S (12) VREF	1.3	
6	V_{REG}	Rpple filter of power supply	- T Vcc	2.6	
16	V_{REF}	Reference voltage		1.3	
7	PW OUT _A		- √cc		
10	PW OUT _B	Output of power amplifier	to DC volume 7 (10)	1.3	
8	PW GND	_			
9	V _{CC}	_		3	
11	V _{CTL}	Input of control voltage for volume control	11-V _{CCC}	П	

Application Note

- (1) A volume which has the characteristic "curve A" is available for the DC volume control.
- (2) The capacitor C is used for absorbing volume sliding noise.
- (3) The DC volume control circuit is applicable to "function of mute", connecting as Fig.1.
 - In case of tuning mute–on, the load of "reference voltage circuit" is R, at maximum volume.
- (4) Small temperature coefficient and excellent frequency characteristic is needed by capacitors below.
 - Oscillation preventing capacitors for power amplifier output.
 - Capacitor between VREF and GND.
 - Capacitor between VCC and GND.
 - Capacitor between VREG and GND.

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Supply voltage	V _{CC}	7	V
Output current	I _{O (peak)}	120	mA
Power dissipation	P _D (Note)	750	mW
Operating temperature	T _{opr}	-25~75	°C
Storage temperature	T _{stg}	-55~150	°C

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(Note) Derated above Ta = 25°C in the proportion of 6mW / °C.

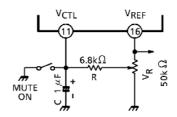
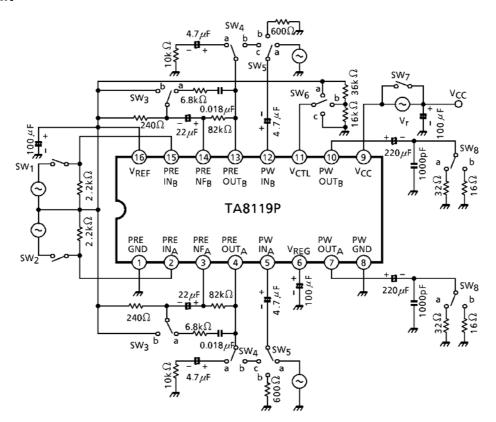


Fig.1 Function of mute

Electrical Characteristics
Unless Otherwise Specified, V_{CC} = 3V, Ta = 25°C, f = 1kHz
Preamplifier: R_L = 10k Ω , Vol = Min
Power Amplifier: R_L = 32 Ω , Vol = Max

	Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit	
Oui	escent supply current		I _{CCQ1}	_	V _{in} = 0, Vol = min	_	9.0	13.0	mA	
Quiescent supply current			I _{CCQ2}	_	V _{in} = 0, Vol = max	_	11.0	_	ША	
Preamplifier section	Open loop voltage gain	G _{VO}	_	$V_0 = -12 dBV$	55	62	_	dB		
	Closed loop voltage gain	G _{VC}	_	NAB = 1kHz, $V_0 = -12dBV$		33	_	dB		
	Maximum output voltage	V _{om}	_	THD = 1%	600	720	_	mV _{rms}		
	Total harmonic distortion	THD1	_	V _o = -12dBV — 0.04			0.1	%		
	Equivalent input noise voltage	V _{ni}	_	$R_{g} = 2.2k\Omega$ BPF = 30Hz~20kHz NAB (G _V = 33dB, f = 1kHz)			2.0	μV _{rms}		
	Ripple rejection ratio		RR1	_	$R_g = 2.2k\Omega$ V _r = -22dBV, f _r = 100Hz	_	46	_	dB	
	Output power	(1)	P _{o1}	_	THD = 10% 20		27	_	mW	
tion	Output power	(2)	P _{o2}	_	$R_L = 16\Omega$, THD = 10%	_	39	_	11100	
	Voltage gain (1)		G _{V1}		V _O = -12dBV	28	30	32	dB	
tion	Channel balance	СВ		V ₀ = -12dbV	_	0	1.5	dB		
sec	Voltage gain (2)	G _{V2}	_	$V_0 = -12$ dBV, Vol = mid	_	15	_	dB		
lifier	Total harmonic distortion		THD2		P ₀ = 10mW	_	0.5	1.2	- %	
amb			THD3		P ₀ = 10mW, Vol = mid	_	0.3	_	/0	
Power amplifier section	Output noise voltage	V _{no}	_	R_g = 600 Ω BPF = 30Hz~20kHz	_	250	320	μV _{rms}		
	Maximum attenuation	ATT	_	V _o = −12dBV Vol = max→min	66	72	_	dB		
	Ripple rejection ratio	RR2	_	$R_g = 600\Omega$ V _r = -22dBV, f _r = 100Hz — 46		_	dB			
Total	Cross talk (ch-A / ch-B)		СТ	_	$R_g = 2.2k\Omega$ $V_0 = -12dBV$, $Vol = max$	34	40	_	dB	

Test Circuit



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Switch State For Electrical Characteristics

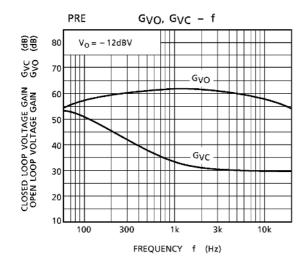
Characteristic	SW ₁	SW ₂	SW ₃	SW ₄	SW ₅	SW ₆	SW ₇	SW ₈
I _{CCQ1}	×	×	а	а	b	С	0	а
I _{CCQ2}	×	×	а	а	b	а	0	а
G _{VO}	0	0	b	а	b	С	0	а
G _{VC}	0	0	а	а	b	С	0	а
V _{om}	0	0	а	а	b	С	0	а
THD1	0	0	а	а	b	С	0	а
V _{ni}	×	×	а	а	b	С	0	а
RR1	×	×	а	а	b	С	×	а
P _{o1}	×	×	а	а	а	а	0	а
P _{o2}	×	×	а	а	а	а	0	b
G _{V1}	×	×	а	а	а	а	0	а
СВ	×	×	а	а	а	а	0	а
G _{V2}	×	×	а	а	а	b	0	а
THD2	×	×	а	а	а	а	0	а
THD3	×	×	а	а	а	b	0	а
V _{no}	×	×	а	а	b	а	0	а
ATT	×	×	а	а	а	a→c	0	а
RR2	×	×	а	а	b	С	×	а
СТ	o / ×	×/0	а	b	С	а	0	а

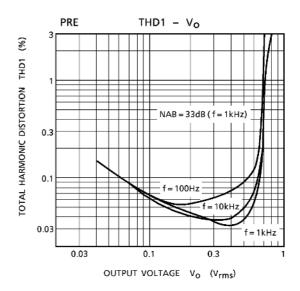
o: Short x: Open

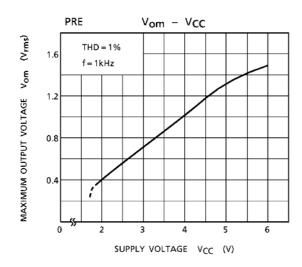
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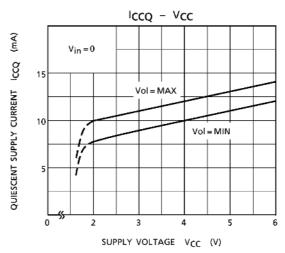
Characteristic Curves

Unless Otherwise Specified: V_{CC} = 3V, f = 1kHz, Ta = 25°C Preamplifier: R_L = 10k Ω , Vol = Min Power Amplifier: R_L = 32 Ω , Vol = Max









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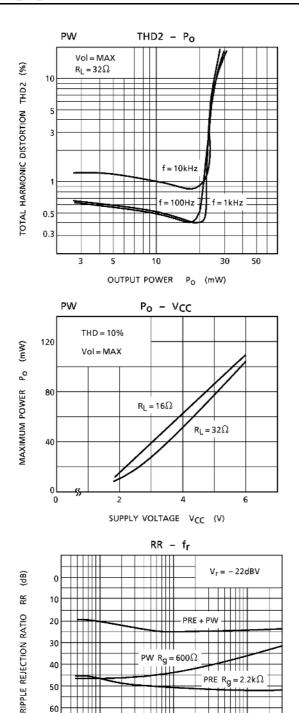
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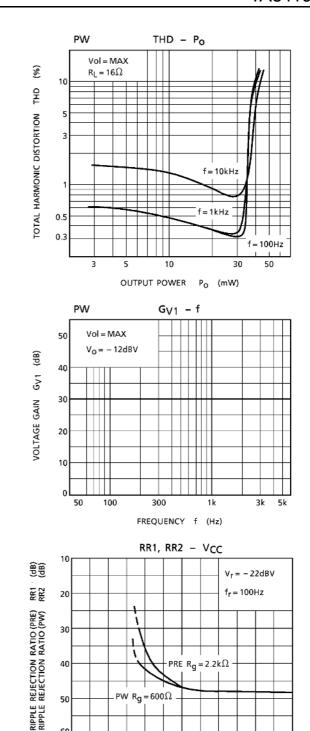
100

300

RIPPLE FREQUENCY fr (Hz)

10k

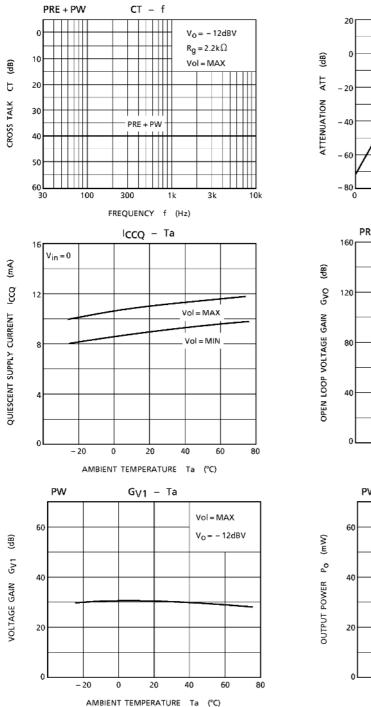


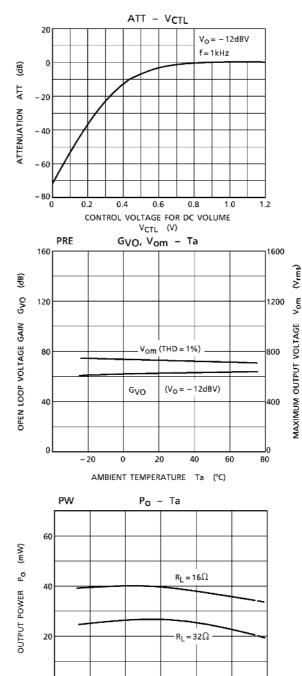


SUPPLY VOLTAGE VCC (V)

8

60 L





- 20

9

0

20

AMBIENT TEMPERATURE Ta (°C)

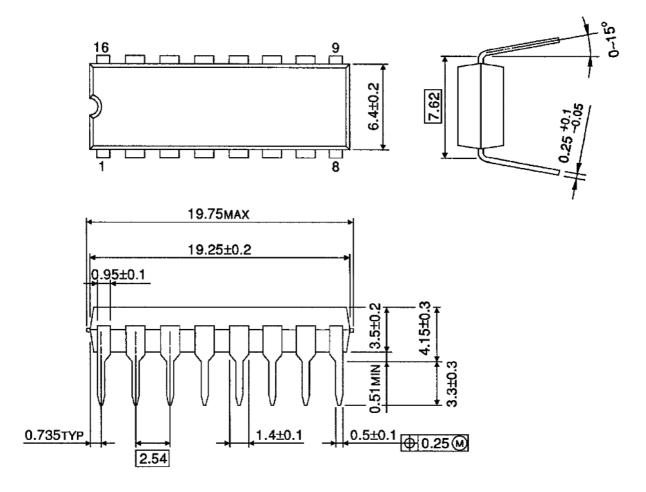
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80

Package Dimensions

DIP16-P-300-2.54A Unit: mm



Weight: 1.00g (typ.)

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